

74AVCH4T245

4 Bit Dual Power Supply Translating Buffer With 3 State Outputs

Description

The 74AVCH4T245 device is 4-bit, dual supply transceiver that enables bidirectional level translation, designed for asynchronous communication between two data buses. It features four 2-bit input-output ports (nAn and nBn), a direction control input (nDIR), an output enable input (nOE) and dual supply pins (VCC(A) and VCC(B)). Both VCC(A) and VCC(B) can be supplied at any voltage between 0.8 V and 3.6 V making the device suitable for translating between any of the low voltage nodes (0.8V, 1.2V, 1.5V, 1.8V, 2.5V and 3.3V). Pins nAn, nOE and nDIR are referenced to VCC(A) and pins nBn are referenced to VCC(B). A HIGH on nDIR allows transmission from nAn to nBn and a LOW on nDIR allows transmission from nBn to nAn. The output enable input (nOE) can be used to disable the outputs so the buses are effectively isolated. The device is fully specified for partial power-down applications using IOFF. The IOFF circuitry disables the output, preventing any damaging back flow current through the device when it is powered down. In suspend mode when either VCC(A) or VCC(B) are at GND level, both nAn and nBn are in the high-impedance OFF-state. The 74AVCH4T245 has active bus hold circuitry which is provided to hold unused or floating data inputs at a valid logic level. This feature eliminates the need for external pull-up or pull-down resistors.

The 74AVCH4T245 is available in the packages, and is specified for operation from -40°C to +125°C among all supply voltages. The wide temperature ranges and high ESD tolerance facilitate their use in harsh applications.

Application(s)

- Personal Electronics
- Industrial
- Enterprise
- Telecom

Features

- Supply Voltage Range: VCC(A)/ VCC(B): from 0.8V to 3.6V
- Max Data Rates:
 - 380Mbps (1.8V to 3.3V Translation)
 - 200Mbps (<1.8V to 3.3V Translation)
 - 200Mbps (Translate to 2.5V or 1.8V)
 - 150Mbps (Translate to 1.5V)
 - 100Mbps (Translate to 1.2V)
 - 50Mbps (Translate to 0.8V~1.1V)
- High Drive Strength (±12mA at 3.3V)
- IOFF Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22
 - Exceeds 5000V Human Body Model (A114)
 - Exceeds 1500V Charged Device Model (C101)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. “Green” Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative.
<https://www.diodes.com/quality/product-definitions/>

Ordering Information

Orderable Part Number	Package Code	Package Description
74AVCH4T245T16-13	T16	TSSOP-16
74AVCH4T245PB-7	PB	U-QFN1826-16
74AVCH4T245ZSA16-7	ZSA16	VQFN3525-16

Notes:

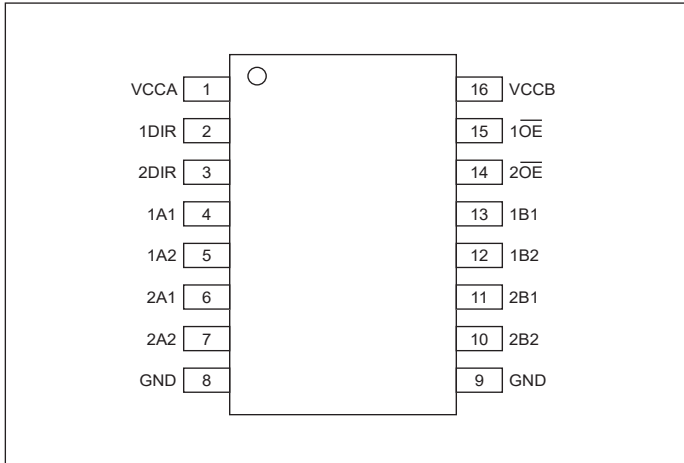
- 7: 7" Tape & Reel, 13: 13" Tape & Reel

Notes:

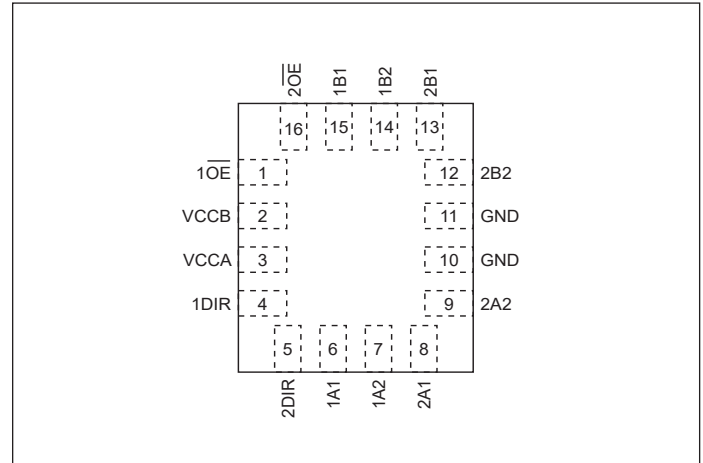
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated’s definitions of Halogen- and Antimony-free, “Green” and Lead-free.
3. Halogen- and Antimony-free “Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Pin Configuration

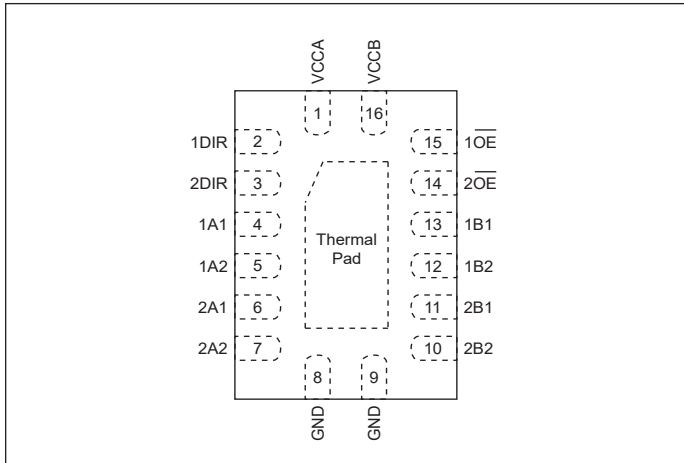
TSSOP (T16) Package



UQFN1826 (PB) Package



VQFN3525 (ZSA16) Package



Pin Description

Pin Number		Pin Name	Signal Type	Description
TSSOP-16 V-QFN3525-16	U-QFN1826-16			
1	3	VCCA	Power	A port supply Voltage
2	4	1DIR	Control Logic Input	Direction Control Pin for Port "1".
3	5	2DIR	Control Logic Input	Direction Control Pin for Port "2".
4	6	1A1	I/O	Input/Output 1A1. Referenced to VCCA.
5	7	1A2	I/O	Input/Output 1A2. Referenced to VCCA.
6	8	2A1	Power	Input/Output 2A1. Referenced to VCCA.

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Pin Number		Pin Name	Signal Type	Description
TSSOP-16 V-QFN3525-16	U-QFN1826-16			
7	9	2A2	I/O	Input/Output 2A2. Referenced to VCCA.
8	10	GND	Power	Ground
9	11	GND	Power	Ground
10	12	2B2	I/O	Input/Output 2B2. Referenced to VCCB.
11	13	2B1	I/O	Input/Output 2B1. Referenced to VCCB.
12	14	1B2	I/O	Input/Output 1B2. Referenced to VCCB.
13	15	1B1	I/O	Input/Output 1B1. Referenced to VCCB.
14	16	$\overline{2OE}$	Control Logic Input	3-state output-mode enable. Pull to High to place port “2” outputs in high-impedance mode. Referenced to VCCA.
15	1	$\overline{1OE}$	Control Logic Input	3-state output-mode enable. Pull to High to place port “1” outputs in high-impedance mode. Referenced to VCCA.
16	2	VCCB	Power	B port supply Voltage

Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Storage Temperature	-65°C to +150°C
Junction Temperature	+150°C
Supply Voltage Range	-0.5V to +4.6V
Input Voltage Range	-0.5V to +4.6V
Voltage Applied to Output in High Impedance or I _{OFF} State....	-0.5V to +4.6V
Voltage Applied to Output in High or Low State.....	-0.5V to V _{CCO} +0.5V
Input Clamp Current V _I < 0	-50mA
Output Clamp Current	-50mA
Continuous Output Current	±50mA
Continuous Current Through V _{CCA} or GND	±100mA
ESD: HBM.....	5KV
ESD: CDM.....	1.5KV

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Thermal Information

Symbol	Parameter	Package	Min.	Typ.	Max.	Units
θ _{JA}	Thermal Resistance Junction-to-Ambient	TSSOP-16		100		°C/W
		U-QFN1826-16		140		
		V-QFN3525-16		60		
θ _{JC}	Thermal Resistance Junction-to-Case	TSSOP-16		43		°C/W
		U-QFN1826-16		80		
		V-QFN3525-16		42		

Note: Test condition for each of the 2 package types: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Recommended Operating Conditions

T_A = +25°C

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{CCA}	Operating Voltage		0.8		3.6	V
V _{CCB}	Operating Voltage		0.8		3.6	V
I _{OH}	High-Level Output Current Data Input, nDIR, OE Input	V _{CCO} = 1.1V			-3	mA
		V _{CCO} = 1.4V to 1.6V			-6	
		V _{CCO} = 1.65V to 1.95V			-8	
		V _{CCO} = 2.3V to 2.7V			-9	
		V _{CCO} = 3V to 3.6V			-12	
I _{OL}	Low-Level Output Current Data Input, nDIR, OE Input	V _{CCO} = 1.1V			3	mA
		V _{CCO} = 1.4V to 1.6V			6	
		V _{CCO} = 1.65V to 1.95V			8	
		V _{CCO} = 2.3V to 2.7V			9	
		V _{CCO} = 3V to 3.6V			12	

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _I	Input Voltage		0		3.6	V
V _O	Output Voltage	Active State	0		V _{CCO}	V
		Tri-State	0		3.6	
T _A	Operating Free-Air Temperature		-40		+125	°C

Electrical Characteristics

T_A = +40°C to +125°C, unless otherwise specified.

Symbol	Parameter	Test Conditions	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Units
			Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High-level input voltage	Data Input, nDIR, nOE Input	V _{CCI} = 0.8V	0.70V _{CCI}	0.70V _{CCI}		0.70V _{CCI}	0.70V _{CCI}	V	
			V _{CCI} = 1.1V to 1.95V	0.65V _{CCI}	0.65V _{CCI}		0.65V _{CCI}	0.65V _{CCI}		
			V _{CCI} = 1.95V to 2.7V	1.6	1.6		1.6	1.6		
			V _{CCI} = 2.7V to 3.6V	2	2		2	2		
V _{IL}	Low-level input voltage	Data Input, nDIR, nOE Input	V _{CCI} = 0.8V				0.3V _{CCI}	0.3V _{CCI}	V	
			V _{CCI} = 1.1V to 1.95V				0.35V _{CCI}	0.35V _{CCI}		
			V _{CCI} = 1.95V to 2.7V				0.7	0.7		
			V _{CCI} = 2.7V to 3.6V				0.8	0.8		
V _{OH}	High-Level Output Voltage	I _{OH} = -0.1mA; V _{CCI} & V _{CCO} = 0.8-3.6V				V _{CCO} -0.1	V _{CCO} -0.1	V		
		I _{OH} = -3mA; V _{CCI} & V _{CCO} = 1.1V	0.95	0.95		0.85	0.85			
		I _{OH} = -6mA; V _{CCI} & V _{CCO} = 1.4V	1.05	1.05		1.05	1.05			
		I _{OH} = -8mA; V _{CCI} & V _{CCO} = 1.65V	1.2	1.2		1.2	1.2			
		I _{OH} = -9mA; V _{CCI} & V _{CCO} = 2.3V	1.75	1.75		1.75	1.75			
		I _{OH} = -12mA; V _{CCI} & V _{CCO} = 3V	2.3	2.3		2.3	2.3			

Symbol	Parameter	Test Conditions	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Units
			Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V _{OL}	Low-Level Output Voltage	I _{OH} = 0.1mA; V _{CCI} & V _{CCO} = 0.8-3.6V	0.1	0.1				0.1		V
		I _{OH} = 3mA; V _{CCI} & V _{CCO} = 1.1V	0.25	0.25				0.25		
		I _{OH} = 6mA; V _{CCI} & V _{CCO} = 1.4V	0.35	0.35				0.35		
		I _{OH} = 8mA; V _{CCI} & V _{CCO} = 1.65V	0.45	0.45				0.45		
		I _{OH} = 9mA; V _{CCI} & V _{CCO} = 2.3V	0.55	0.55				0.55		
		I _{OH} = 12mA; V _{CCI} & V _{CCO} = 3V	0.7	0.7				0.7		
I _I	Input Current	V _I = V _{CCA} or GND; V _{CCI} & V _{CCO} = 0.8-3.6V			±1		±1.5		±1.5	uA
I _{OFF}	Off State Current	A or B Port; V _I or V _O = 0 to 3.6V	V _{CCI} = 0		±1		±3		±10	uA
			V _{CCI} = 0.8-3.6V		±1		±3		±10	
I _{OZ}	High-Z State Current	A or B Port; V _I or V _O = 0 to 3.6V; V _{CCI} = 3.6V			±1		±2		±10	uA
		A Port; V _I or V _O = 0 to 3.6V; V _{CCI} = 3.6V			±1		±2		±5	
		B Port; V _I or V _O = 0 to 3.6V; V _{CCI} = 0			±1		±2		±5	
I _{CCA}	Supply Current	V _I = V _{CCI} or GND IO = 0	V _{CCI} & V _{CCO} = 0.8-3.6V		±2		±10		±35	uA
			V _{CCI} & V _{CCO} = 0.8-1.1V		±1.5		±8		±25	
			V _{CCI} = 0-3.6V; V _{CCO} = 0		±1.5		±10		±35	
			V _{CCI} = 0; V _{CCO} = 0-3.6V		±1		±1		±1	
I _{CCB}	Supply Current	V _I = V _{CCI} or GND IO = 0	V _{CCI} & V _{CCO} = 0.8-3.6V		±2		±10		±35	uA
			V _{CCI} & V _{CCO} = 0.8-1.1V		±1.5		±8		±25	
			V _{CCI} = 0-3.6V; V _{CCO} = 0		±1		±1		±1	
			V _{CCI} = 0; V _{CCO} = 0-3.6V		±1.5		±10		±35	
I _{CCA} + I _{CCB}	Supply Current	V _I = V _{CCI} or GND IO = 0; V _{CCI} & V _{CCO} = 0.8-3.6V			±4		±20		±70	uA

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Symbol	Parameter	Test Conditions	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Units
			Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
C _I	Control Input Capacitance	nDIR, n $\overline{\text{OE}}$ Input; V _I = 3.3V or GND; V _{CCI} = 3.3V		3.5			4.5		4.5	pF
C _O	Input/Output Capacitance	A or B; V _O = 3.3V or GND; V _{CCI} & V _{CCO} = 3.3V		6			7		7	pF

Switching Characteristics

V_{CCA} = 0.8V; T_A = -40°C to +125°C, unless otherwise specified.

Parameter	Test Conditions	Direction	V _{CCB}															Units			
			0.8V			1.2V ± 0.1V			1.5V ± 0.1V			1.8V ± 0.15V			2.5V ± 0.2V				3.3V ± 0.3V		
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.		Min.	Typ.	Max.
tpd	Propagation delay	nAn to nBn		11.0			7.3			6.5			6.2			6.5			7.0	ns	
		nBn to nAn		11.0			10.0			12.4			12.3			12.1			12.0		
ten	Enable Time	n $\overline{\text{OE}}$ to nAn		18.2			18.2			18.2			18.2			18.2			18.2	ns	
		n $\overline{\text{OE}}$ to nBn		19.2			12.7			11.4			10.9			10.7			11.1		
tdis	Disable Time	n $\overline{\text{OE}}$ to nAn		14.3			14.3			14.3			14.3			14.3			14.3	ns	
		n $\overline{\text{OE}}$ to nBn		12.6			9.9			9.0			9.4			9.0			9.7		

V_{CCB} = 0.8V; T_A = -40°C to +125°C, unless otherwise specified.

Parameter	Test Conditions	Direction	V _{CCA}															Units			
			0.8V			1.2V ± 0.1V			1.5V ± 0.1V			1.8V ± 0.15V			2.5V ± 0.2V				3.3V ± 0.3V		
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.		Min.	Typ.	Max.
tpd	Propagation delay	nAn to nBn		14.5			12.7			12.4			12.3			12.1			12.0	ns	
		nBn to nAn		14.5			7.3			6.5			6.2			5.9			6.0		
ten	Enable Time	n $\overline{\text{OE}}$ to nAn		18.2			13.0			12.1			9.6			7.3			6.4	ns	
		n $\overline{\text{OE}}$ to nBn		19.2			15.8			15.3			15.0			15.0			14.8		
tdis	Disable Time	n $\overline{\text{OE}}$ to nAn		14.3			9.6			8.5			7.5			7.7			8.6	ns	
		n $\overline{\text{OE}}$ to nBn		17.0			13.8			13.4			13.1			12.9			12.7		

V_{CCA} = 1.2V ± 0.1V; T_A = -40°C to +125°C, unless otherwise specified.

Parameter	Test Conditions	Direction	V _{CCB}															Units
			1.2V ± 0.1V			1.5V ± 0.1V			1.8V ± 0.15V			2.5V ± 0.2V			3.3V ± 0.3V			
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
tpd	Propagation delay	nAn to nBn	0.5	3	8.3	0.5	2.9	6.3	0.5	2.1	5.5	0.5	2.1	4.6	0.5	2.3	4.6	ns
		nBn to nAn	0.5	3	8.3	0.5	3.1	7.8	0.5	2.8	7.7	0.5	2.1	7.4	0.5	2.2	7.3	
ten	Enable Time	n $\overline{\text{OE}}$ to nAn	1.8	3.9	11.7	1.8	4.2	11.7	1.8	4.3	11.7	1.8	3.5	11.7	1.8	3.5	11.7	ns
		n $\overline{\text{OE}}$ to nBn	1.9	4	13.0	1.9	2.5	9.5	1.9	3.3	8.2	1.4	3.6	7.9	1.2	4.5	7.7	
tdis	Disable Time	n $\overline{\text{OE}}$ to nAn	1.4	3.2	11.5	1.4	2.3	11.5	1.4	3	11.5	1.4	3	11.5	1.4	3.1	11.5	ns
		n $\overline{\text{OE}}$ to nBn	1.1	3	10.0	1.1	2.2	8.1	1.1	2.9	7.5	1.0	2.5	6.3	1.0	5.5	6.3	

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$V_{CCA} = 1.5V \pm 0.1V$; $T_A = -40^{\circ}C$ to $+125^{\circ}C$, unless otherwise specified.

Parameter	Test Conditions	Direction	V_{CCB}															Units
			1.2V ± 0.1V			1.5V ± 0.1V			1.8V ± 0.15V			2.5V ± 0.2V			3.3V ± 0.3V			
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
tpd	Propagation delay	nAn to nBn	0.3		7.8	0.3		6.3	0.3		5.2	0.4		4.2	0.4		4.2	ns
		nBn to nAn	0.7		6.3	0.7		6.3	0.5		5.9	0.4		5.7	0.3		5.6	
ten	Enable Time	nOE to nAn	1.8		10.5	1.4		9.6	1.1		9.5	0.7		9.7	0.4		9.4	
		nOE to nBn	1.9		11.0	1.4		9.6	1.1		7.7	0.9		7.1	0.9		6.9	
tdis	Disable Time	nOE to nAn	1.1		10.2	1.8		10.2	1.5		10.2	1.3		10.2	1.6		10.2	
		nOE to nBn	1.4		10.4	1.9		10.3	1.9		9.1	1.4		7.4	1.2		7.6	

$V_{CCA} = 1.8V \pm 0.15V$; $T_A = -40^{\circ}C$ to $+125^{\circ}C$, unless otherwise specified.

Parameter	Test Conditions	Direction	V_{CCB}															Units
			1.2V ± 0.1V			1.5V ± 0.1V			1.8V ± 0.15V			2.5V ± 0.2V			3.3V ± 0.3V			
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
tpd	Propagation delay	nAn to nBn	0.1		7.7	0.1		5.9	0.1		4.9	0.1		3.9	0.3		3.9	ns
		nBn to nAn	0.6		5.5	0.6		5.3	0.5		4.9	0.3		4.6	0.3		4.5	
ten	Enable Time	nOE to nAn	1.8		9.0	1		8.6	1		7.3	0.6		7.3	0.4		7.2	
		nOE to nBn	1.7		10.5	1.2		9.2	1		7.4	0.8		6.7	0.8		6.5	
tdis	Disable Time	nOE to nAn	1.0		8.9	1.6		8.6	1.8		8.7	1.3		8.7	1.6		8.7	
		nOE to nBn	1.2		10.0	1.7		9.9	1.6		8.7	1.2		7.4	1		6.9	

$V_{CCA} = 2.5V \pm 0.2V$; $T_A = -40^{\circ}C$ to $+125^{\circ}C$, unless otherwise specified.

Parameter	Test Conditions	Direction	V_{CCB}															Units
			1.2V ± 0.1V			1.5V ± 0.1V			1.8V ± 0.15V			2.5V ± 0.2V			3.3V ± 0.3V			
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
tpd	Propagation delay	nAn to nBn	0.1		7.4	0.1		5.7	0.1		4.6	0.2		3.9	0.1		3.6	ns
		nBn to nAn	0.6		4.6	0.6		4.2	0.4		4.1	0.2		3.9	0.2		3.3	
ten	Enable Time	nOE to nAn	1.0		8.0	0.7		6.7	0.7		6.5	0.6		5.9	0.4		4.8	
		nOE to nBn	1.5		9.8	0.9		8.8	0.8		7.0	0.6		5.8	0.6		4	
tdis	Disable Time	nOE to nAn	0.7		9.0	1		8.4	1		8.4	1		6.2	1		6.6	
		nOE to nBn	0.9		9.9	1.5		9.4	1.3		8.2	1.1		6.2	0.9		5.2	

$V_{CCA} = 3.3V \pm 0.3V$; $T_A = -40^{\circ}C$ to $+125^{\circ}C$, unless otherwise specified.

Parameter	Test Conditions	Direction	V_{CCB}															Units
			1.2V ± 0.1V			1.5V ± 0.1V			1.8V ± 0.15V			2.5V ± 0.2V			3.3V ± 0.3V			
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
tpd	Propagation delay	nAn to nBn	0.1		7.3	0.1		5.6	0.1		4.5	0.1		3.7	0.1		2.9	ns
		nBn to nAn	0.6		4.6	0.6		4.2	0.4		3.9	0.2		3.7	0.1		2.8	
ten	Enable Time	nOE to nAn	0.7		9.2	0.6		8.7	0.6		5.9	0.6		5.6	0.4		3.8	
		nOE to nBn	1.4		9.5	0.8		8.7	0.6		6.8	0.5		5.7	0.5		3.8	
tdis	Disable Time	nOE to nAn	0.6		9.5	0.7		9.3	0.7		8.3	0.7		5.6	0.7		6.6	
		nOE to nBn	0.8		9.5	1.4		9.3	1.2		8.1	1		6.4	0.8		6.2	

Operating Characteristics

$T_A = +25^\circ\text{C}$

Parameter	Test Conditions		0.8V	1.2V	1.5V	1.8V	2.5V	3.3V	Units
CpdA	A to B	Enabled	0.2	0.2	0.2	0.2	0.3	0.4	pF
		Disabled	0.2	0.2	0.2	0.2	0.3	0.4	
	B to A	Enabled	9.5	9.7	9.8	9.9	10.7	11.9	
		Disabled	0.6	0.6	0.6	0.6	0.7	0.7	
CpdY	A to B	Enabled	9.5	9.7	9.8	9.9	10.7	11.9	
		Disabled	0.6	0.6	0.6	0.6	0.7	0.7	
	B to A	Enabled	0.2	0.2	0.2	0.2	0.3	0.4	
		Disabled	0.2	0.2	0.2	0.2	0.3	0.4	

Parameter Measurement Information

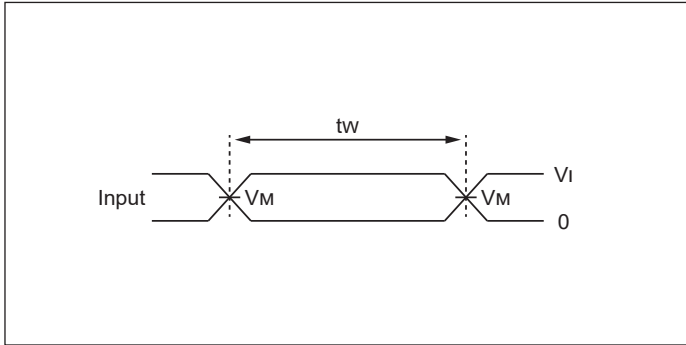


Figure 1. Voltage Waveform Pulse Duration

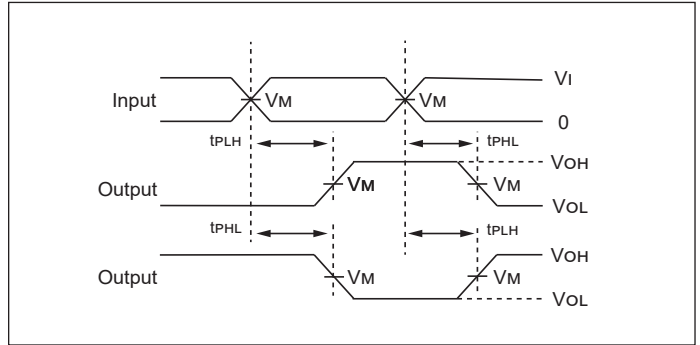


Figure 2. Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

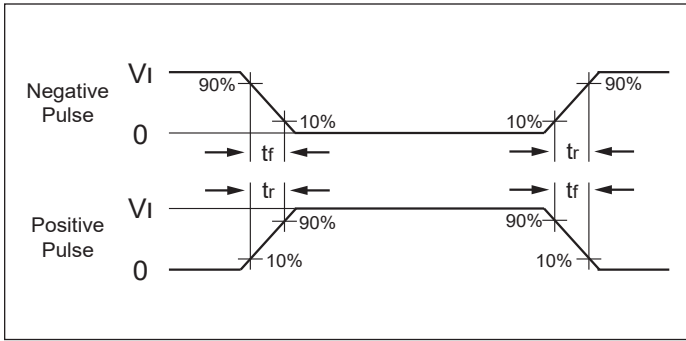


Figure 3. The Vi Source Waveform

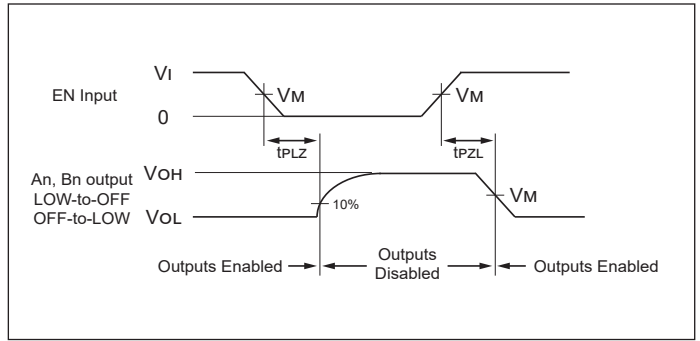


Figure 4. The Enable/Disable (EN) to Output (Yn) Times

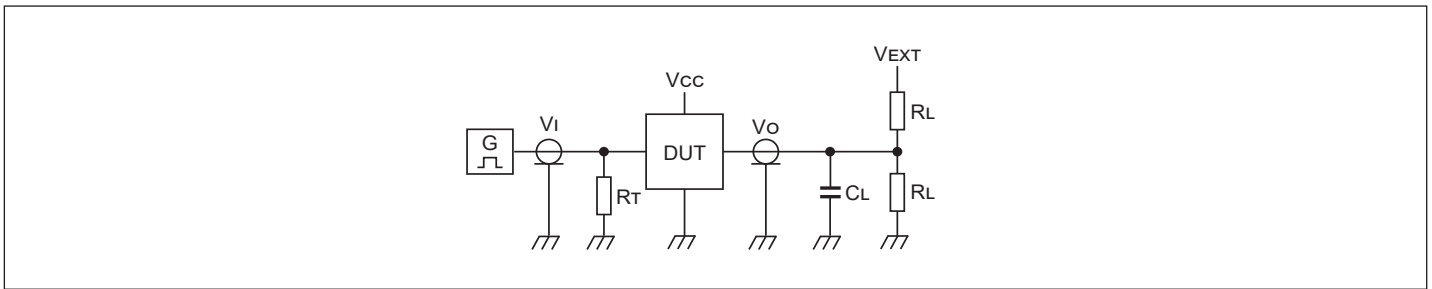


Figure 5. Load Circuit and Voltage Waveforms

Parameter	S1
tpd	Open
ten/ tdis	2*VCCO
ten/ tdis	GND

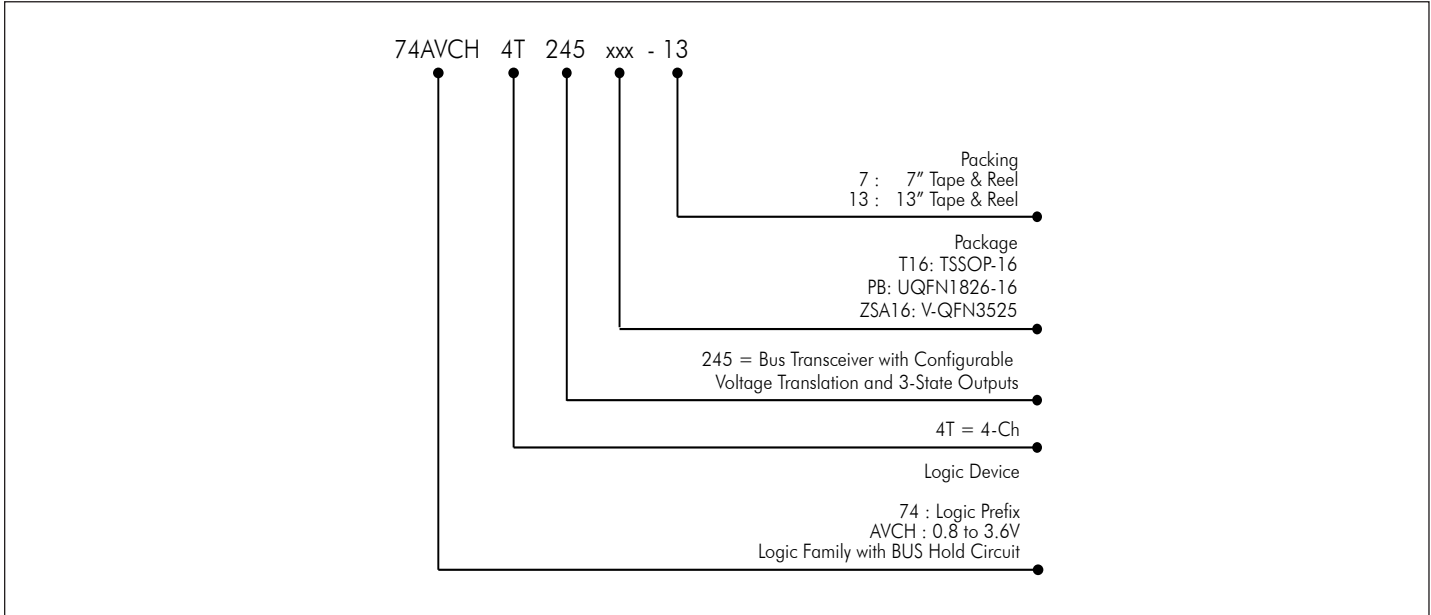
VCC	RL	CL	VTP
0.8V-1.6V	2KΩ	15pF	0.1V
1.65V-2.7V	2KΩ	15pF	0.15V
3.0V-3.6V	2KΩ	15pF	0.3V

Notes:

1. Includes test lead and test apparatus capacitance.
2. $f = 1\text{MHz}$, $\Delta t/\Delta V < 1\text{ns/V}$
3. t_{PLH} and t_{PHL} are the same as t_{pD} .
4. $t_r, t_f < 1\text{ns}$

74AVCH4T245

Device Naming Information



Part Marking

TSSOP (T) Package

Logo

AVCH4T245
YY WW XX

Identification Code: AVCH4T245
YY: Year: 24, 25, 26~
WW: Workweek: 01~52;
52 represents 52 and 53 week
XX: Internal Code

UQFN (PB) Package

XX
Y W X

XX: Z5 = Identification Code
Y: Year: 0~9
W: Week: A~Z: week 1~26;
a~z: week 27~52; z represents 52 and 53 week
X: Internal Code

VQFN (ZSA) Package

XX
Y W X

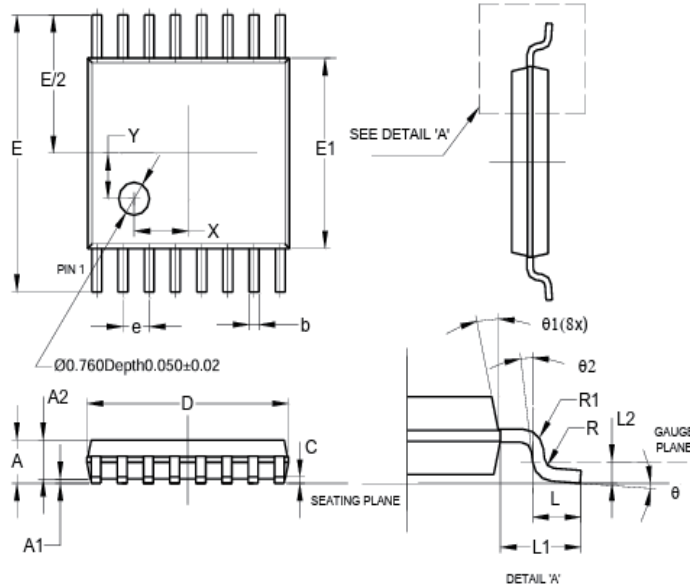
XX: 2W = Identification Code
Y: Year: 0~9
W: Week: A~Z: week 1~26;
a~z: week 27~52; z represents 52 and 53 week
X: Internal Code

74AVCH4T245

Packaging Mechanical

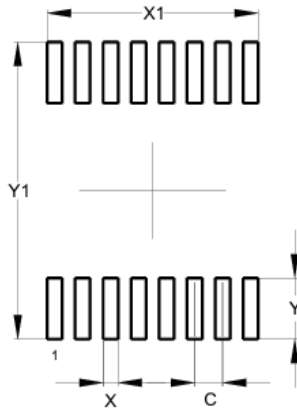
16-TSSOP (T16)

Package Outline Dimensions



TSSOP-16			
Dim	Min	Max	Typ
A	-	1.08	-
A1	0.05	0.15	-
A2	0.80	0.93	-
b	0.19	0.30	-
c	0.09	0.20	-
D	4.90	5.10	-
E	6.40 BSC		
E1	4.30	4.50	-
e	0.65 BSC		
L	0.45	0.75	-
L1	1.00 REF		
L2	0.25 BSC		
R / R1	0.09	-	-
X	-	-	1.350
Y	-	-	1.050
theta	0°	8°	-
theta1	5°	15°	-
theta2	0°	-	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.650
X	0.350
X1	4.900
Y	1.400
Y1	6.800

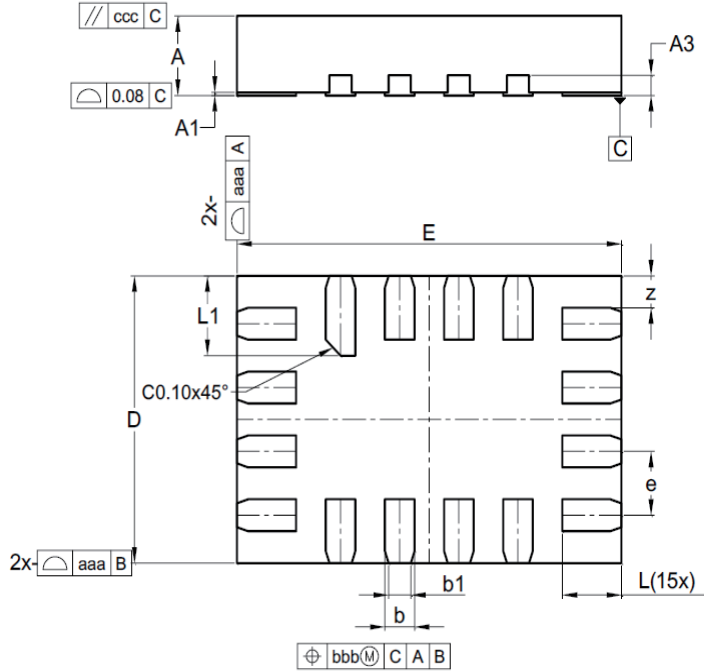
Note: The suggested land pattern dimensions have been provided for reference only, as actual pad layouts may vary depending on application. These dimensions may be modified based on user equipment capability or fabrication criteria. A more robust pattern may be desired for wave soldering and is calculated by adding 0.2 mm to the 'Z' dimension. For further information, please reference document IPC-7351A, Naming Convention for Standard SMT Land Patterns, and for International grid details, please see document IEC, Publication 97.

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

74AVCH4T245

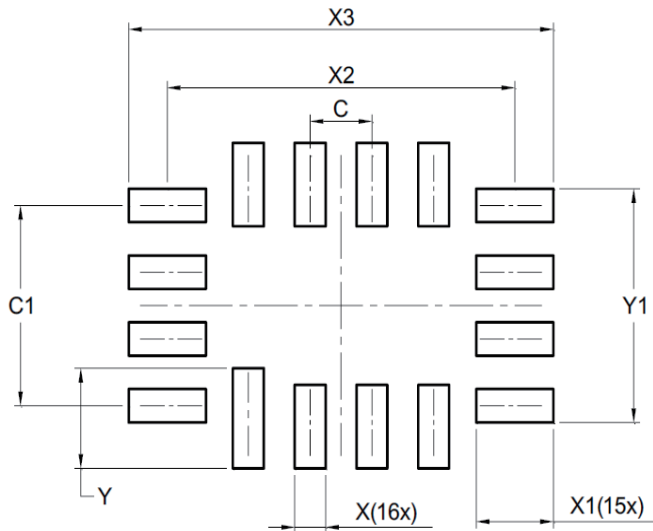
16-U-QFN1826 (PB)

Package Outline Dimensions



U-QFN1826-16 (Type A)			
Dim	Min	Max	Typ
A	0.45	0.55	0.50
A1	0.00	0.05	0.02
A3	--	--	0.127
b	0.15	0.25	0.20
b1	0.10	0.20	0.15
D	1.75	1.85	1.80
E	2.55	2.65	2.60
e	--	--	0.40
L	0.35	0.45	0.40
L1	0.45	0.55	0.50
z	--	--	0.20
aaa	0.250		
bbb	0.100		
ccc	0.100		
All Dimensions in mm			

Suggested Pad Layout

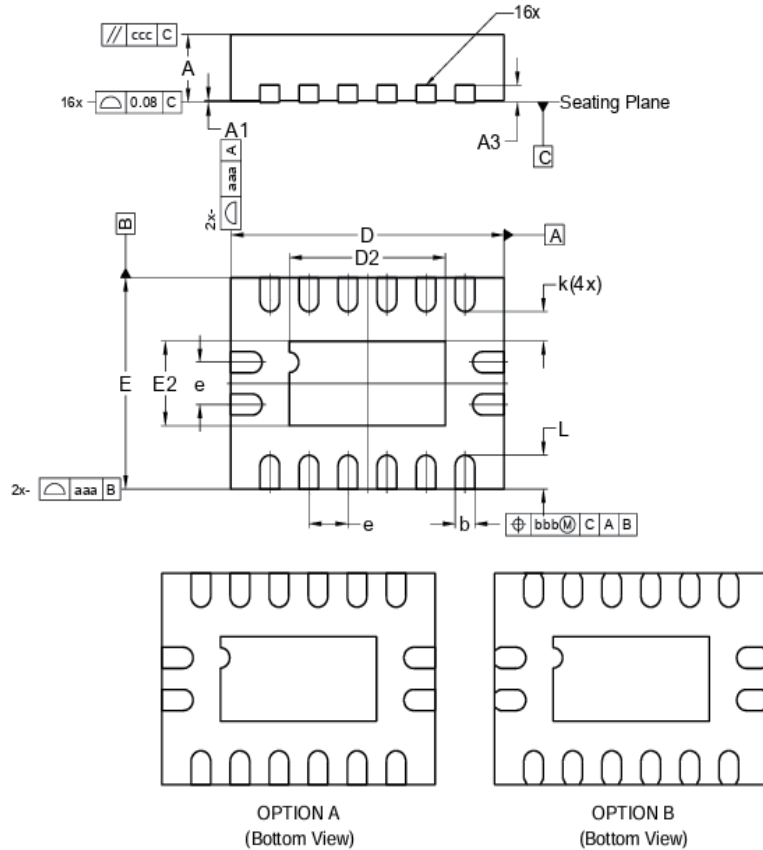


Dimensions	Value (in mm)
C	0.400
C1	1.200
X	0.200
X1	0.500
X2	2.250
X3	2.750
Y	0.600
Y1	1.400

74AVCH4T245

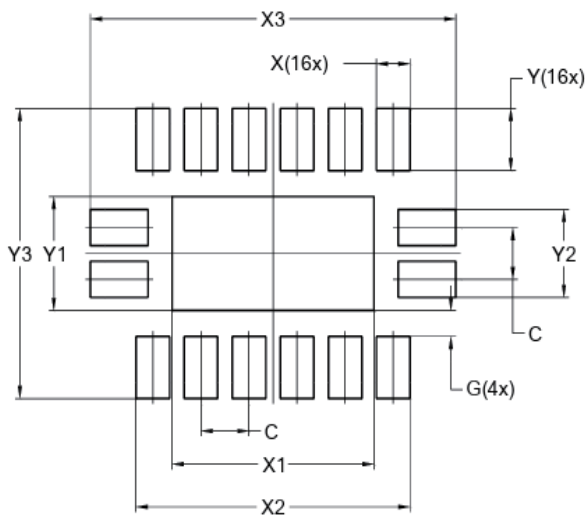
16-V-QFN3525 (ZSA16)

Package Outline Dimensions



V-QFN3525-16 Standard			
Dim	Min	Max	Typ
A	0.75	0.90	--
A1	0.00	0.05	0.02
A3	--	--	0.203
b	0.20	0.30	0.25
D	3.45	3.55	3.50
D2	1.90	2.10	2.00
E	2.45	2.55	2.50
E2	0.90	1.10	1.00
e	0.50 BSC		
k	--	--	0.35
L	0.35	0.45	0.40
aaa	0.250		
bbb	0.100		
ccc	0.100		
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.500
G	0.250
X	0.350
X1	2.100
X2	2.850
X3	3.800
Y	0.600
Y1	1.100
Y2	0.850
Y3	2.800

For latest package information:

See <http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/>.

Mechanical Data

TSSOP-16 (T16)

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 Ⓔ³
- Weight: 0.054811 grams (Approximate)

U-QFN1826-16 (PB)

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - NiPdAu Nickel Palladium Gold. Solderable per MIL-STD-202, Method 208 Ⓔ⁴
- Weight: 0.00639 grams (Approximate)

V-QFN3525-16 (ZSA16)

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - NiPdAu Nickel Palladium Gold, Solderable per MIL-STD-202, Method 208 Ⓔ⁴
- Weight: 0.0143 grams (Approximate)

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